

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	59	kubota near masafumi.in.	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/2 1 16:10	
2	BRS	L2	351	hayashi near shigenori.in.	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/2 1 16:11	
3	BRS	L3	3370	(high near dielectric) near15 (substrate)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/2 1 16:11	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
4	BRS	L4	87	(radiat\$3 or irradiat\$3) near15 (high near dielectric) near15 (substrate)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/2 1 16:16	
5	BRS	L5	4832	(radiat\$3 or irradiat\$3) near15 (insulat\$3) near15 (substrate)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/2 1 16:17	
6	BRS	L7	5	(radiat\$3 or irradiat\$3) near10 (light) near15 (insulat\$3) near15 (constant) near15 (substrate)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/2 1 16:17	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
7	BRS	L6	879	(radiat\$3 or irradiat\$3) near10 (light) near15 (insulat\$3) near15 (substrate)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/2 1 17:49	
8	BRS	L8	66616	film near3 dielectric	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/2 1 17:50	
9	BRS	L9	4773	film near3 (high near dielectric)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/2 1 17:50	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
10	BRS	L10	429	(film near3 (high near dielectric)) near5 substrate	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/2 1 18:16	
11	BRS	L11	61	10 and ((irradiat\$3 or emit\$3) or illuminat\$3)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/2 1 17:51	
12	BRS	L12	4	((film near3 (high near dielectric)) near5 substrate) near9 ((irradiat\$3 or emit\$3) or illuminat\$3)	USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/2 1 18:18	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
13	BRS	L13	1	((film near3 (high near dielectric)) near5 substrate) near15 (laser)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/2 1 18:19	
14	BRS	L14	44	((film near3 (high near dielectric)) near5 substrate) and laser	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/2 1 18:42	
15	BRS	L15	5	(gate) near15 ((film near3 (high near dielectric)) near5 substrate) and laser	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/10/2 1 18:43	

	U	1	Document ID	Title	Current OR	Pages
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20040157473 A1	Method for fabricating semiconductor device	438/785	19
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20040004242 A1	Semiconductor device and method for fabricating the same	257/310	11
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20030113972 A1	Semiconductor device manufacturing method	438/287	23
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20020115304 A1	Manufacturing method for a field-effect transistor, manufacturing method for a semiconductor device, and apparatus therefor	438/769	16
5	<input type="checkbox"/>	<input type="checkbox"/>	US 6747748 B2	Manufacturing method for a field-effect transistor, manufacturing method for a semiconductor device, and apparatus therefor	356/632	15